

## PREFACE

The Seventh International Conference on Silicon Carbide, III-Nitrides and Related Materials (ICSCIII-N'97) held on 31 August to 5 September 1997 in Stockholm, Sweden, was very productive and exciting for the wide bandgap community. In total, 27 countries from the East and West were represented. Some 480 registered participants representing Universities (73%) and Industry (27%) converged on the conference site for five days to share and discuss the spectacular progress made in the last two years.

These proceedings document our present understanding of the many topics of interest, such as the growth of bulk crystals, the growth of epitaxial layers, theoretical approaches, the characterization of the grown material, the development of suitable processes and electronic devices operating under extreme conditions and providing outstanding properties.

Contained in these proceedings are 326 contributed and 22 invited papers which describe the depth and breadth of the activity in this field. The number of papers has exploded to such an extent that, in addition to the two oral parallel sessions, four poster sessions had to be added to accommodate all the accepted papers. Consequently, the conference proceedings appear as a two-volume edition. A kick off and a closing plenary session consisting of an industrial perspective and three summaries of the late breaking news presented at the conference straddled the contributed and invited presentations. The oral sessions and poster presentations attracted much enthusiasms and probing discussions which frequently extended into the social events such as the civic reception in the City Hall and the dinner at the Vasa Museum.

The success of the Seventh International Conference on Silicon Carbide, III-Nitrides and Related Materials was due to the labor of many behind the scene organizers. The International Steering Committee made many valuable suggestions regarding the scientific portion of the conference. The members of the Program Committee spent an inordinate amount of time to carefully review, select and organize the technical program. The session chairmen made sure that the meeting ran very smoothly and on time. We are grateful to all the reviewers who carefully read the manuscripts during the conference in an effort to maintain high scientific standards and quick publication of the proceedings.

The conference would not have been successful had it not been for the expert leadership and assistance of Lena Åberg of the Stockholm Convention Bureau and her staff who diligently took care of all the organizational matters at all stages leading to and during the conference. Lena had an uncanny ability of finding and pushing the right buttons at the right time. We are indebted to her deeply and express our deepest appreciation of her friendly and radiant personality and her help. We are also grateful to Michael Baßler, Kai Christiansen, Thomas Dalibor, Thomas Frank and Thomas Troffer for their dedicated and flawless assistance in organizing the reviewing process before, during and after the conference; they worked as a perfect team.

The generous support of the many industrial and government sponsors of ICSCIII-N'97, listed on a separate page, enabled the organizers to keep the registration fee at a reasonable level as well as to help providing for social activities, meals, beverages and sumptuous fruits.

The next conference in this series will revert to its more familiar name: "International Conference on Silicon Carbide and Related Materials" (ICSCRM). It will be held in North Carolina, USA in 1999. General Chairman will be Dr.C.H.Carter, Jr. We wish the organizers of the next conference much success.

Erlangen, Richmond, Linköping, October 1997

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